DERWENT-ACC-NO: 1977-13583Y
DERWENT-WEEK: 197708

TITLE: Thin film resistor - having silica or alumina oxidn.-preventing layer
and metal layer to stabilise resistance

PATENT-ASSIGNEE: OKI ELECTRIC IND CO LTD[OKID]

PRIORITY-DATA: 1975JP-0078618 (June 26, 1975)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES
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MAIN-IPC
N/A

INT-CL (IPC): B41J003/20; C23C013/00 ; H01C007/00 ; H05K003/10

ABSTRACTED-PUB-NO: JP52003196A
BASIC-ABSTRACT: The method comprises the steps of (1) depositing the thin
resistance layer on a substrate by vacuum deposition (2) forming an oxide.-preventing layer of silicon dioxide or alumina on the thin resistance
layer, (3) forming a metal layer on the oxidn.-preventing layer and (4) heating
the laminated layers in the air to form the resistor.

The resistor is protected with a protecting layer of tantalum pentoxide formed
on the metal layer. The oxidn.-preventing layer prevents oxidn. of the resistance layer. The metal layer consists of Al, Cr, or Ni-Cr. The resistance layer consists of TaN W or Ni-Cr. The metal layer stabilises the
resistance of the resistor.

TITLE-TERMS:
THIN FILM RESISTOR SILICA ALUMINA OXIDATION PREVENT LAYER METAL LAYER STABILISED RESISTANCE

DERWENT-CLASS: L03 P75 V01 V04

CPI-CODES: L03-B01B;